

### General Description

The AAT7126 30V N-Channel Power MOSFET is a member of AnalogicTech™'s TrenchDMOS™ product family. Using the ultra-high density proprietary TrenchDMOS technology, this product demonstrates high power handling and small size.

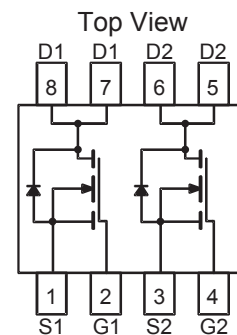
### Features

- $V_{DS(MAX)} = 30V$
- $I_{D(MAX)}^1 = 6.8A @ 25^{\circ}C$
- Low  $R_{DS(ON)}$ :
  - $26 m\Omega @ V_{GS} = 10V$
  - $41 m\Omega @ V_{GS} = 4.5V$

### Applications

- Battery-powered portable equipment
- Laptop computers
- Desktop computers
- DC/DC converters

### Dual SOP-8 Package



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### Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Description	Value	Units	
$V_{DS}$	Drain-Source Voltage	30	V	
$V_{GS}$	Gate-Source Voltage	$\pm 20$		
$I_D$	Continuous Drain Current @ $T_J=150^{\circ}C$ <sup>1</sup>	$T_A = 25^{\circ}C$	$\pm 6.8$	A
		$T_A = 70^{\circ}C$	$\pm 5.4$	
$I_{DM}$	Pulsed Drain Current	$\pm 24$		
$I_S$	Continuous Source Current (Source-Drain Diode) <sup>1</sup>	1.7		
$P_D$	Maximum Power Dissipation <sup>1</sup>	$T_A = 25^{\circ}C$	2.0	W
		$T_A = 70^{\circ}C$	1.25	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	$^{\circ}C$	

### Thermal Characteristics

Symbol	Description	Value	Units
$R_{\theta JA}$	Typical Junction-to-Ambient steady state, one FET on	100	$^{\circ}C/W$
$R_{\theta JA2}$	Industry Standard Junction-to-Ambient Figure, $t < 10$ sec.	62.5	$^{\circ}C/W$
$R_{\theta JC}$	Typical Junction-to-Case, one FET on	35	$^{\circ}C/W$

### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Description	Conditions	Min	Typ	Max	Units
<b>DC Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
R <sub>DS(ON)</sub>	Drain-Source ON-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =6.8A		19.5	26	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.4A		32	41	
I <sub>D(ON)</sub>	On-State Drain Current <sup>2</sup>	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V (Pulsed)	24			A
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.0			V
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
I <sub>DSS</sub>	Drain Source Leakage Current	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V			1	μA
		V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, T <sub>J</sub> =70°C			5	
g <sub>fs</sub>	Forward Transconductance <sup>2</sup>	V <sub>DS</sub> =5V, I <sub>D</sub> =6.8A		14		S
<b>Dynamic Characteristics <sup>3</sup></b>						
Q <sub>G</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =6.8A, V <sub>GS</sub> =5V		8.6	13	nC
Q <sub>GT</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =6.8A, V <sub>GS</sub> =10V		16	24	nC
Q <sub>GS</sub>	Gate-Source Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =6.8A, V <sub>GS</sub> =10V		2.5		nC
Q <sub>GD</sub>	Gate-Drain Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =6.8A, V <sub>GS</sub> =10V		2.8		nC
t <sub>D(ON)</sub>	Turn-ON Delay	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =3Ω, R <sub>G</sub> =6Ω		3		ns
t <sub>R</sub>	Turn-ON Rise Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =3Ω, R <sub>G</sub> =6Ω		3		ns
t <sub>D(OFF)</sub>	Turn-OFF Delay	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =3Ω, R <sub>G</sub> =6Ω		12		ns
t <sub>F</sub>	Turn-OFF Fall Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =3Ω, R <sub>G</sub> =6Ω		6		ns
<b>Source-Drain Diode Characteristics</b>						
V <sub>SD</sub>	Source-Drain Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0, I <sub>S</sub> =1.7A			1.2	V
I <sub>S</sub>	Continuous Diode Current				1.7	A

Note 1: Mounted on 1" x 1" FR4 Copper Board, 10 sec pulse width.

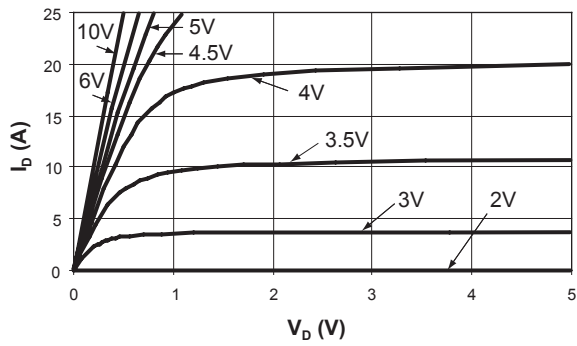
Note 2: Pulse test: pulse width = 300μs

Note 3: Guaranteed by design. Not subjected to production testing.

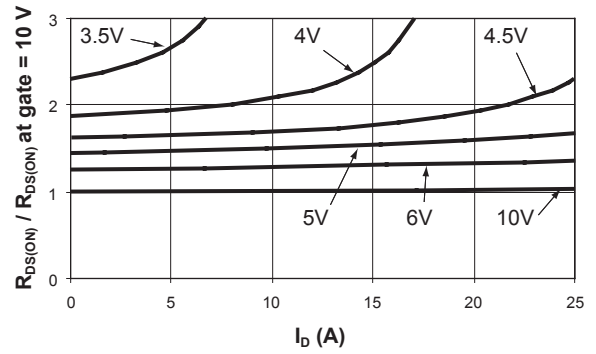
## Typical Characteristics

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

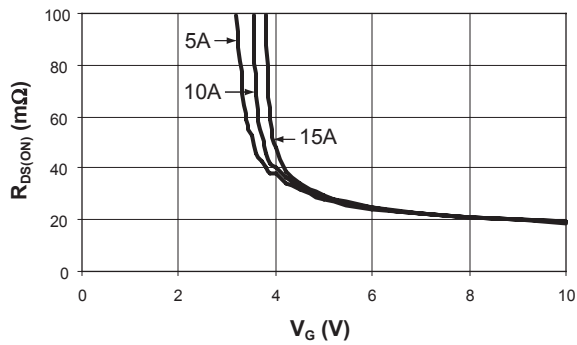
### Forward Characteristics



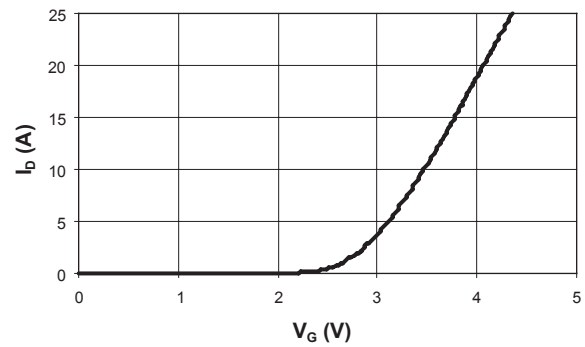
### Normalized $R_{DS(ON)}$



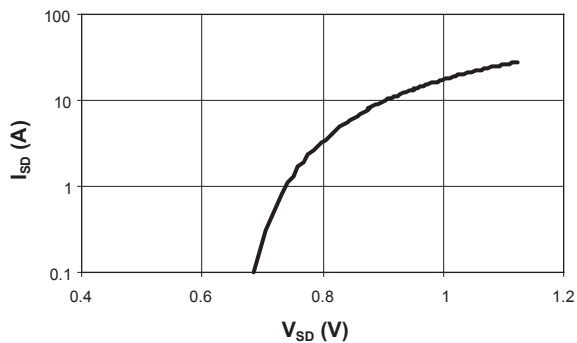
### $R_{DS(ON)}$ vs. $V_G$



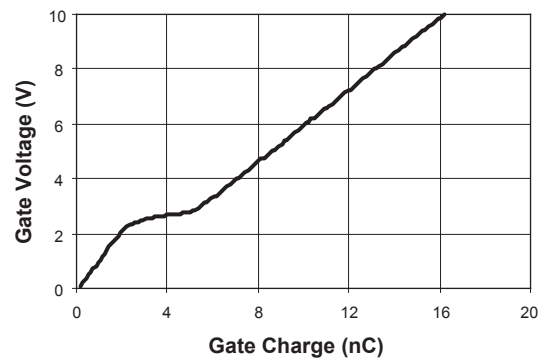
### Transfer



### Source to Drain Voltage



### Gate Charge Characteristics



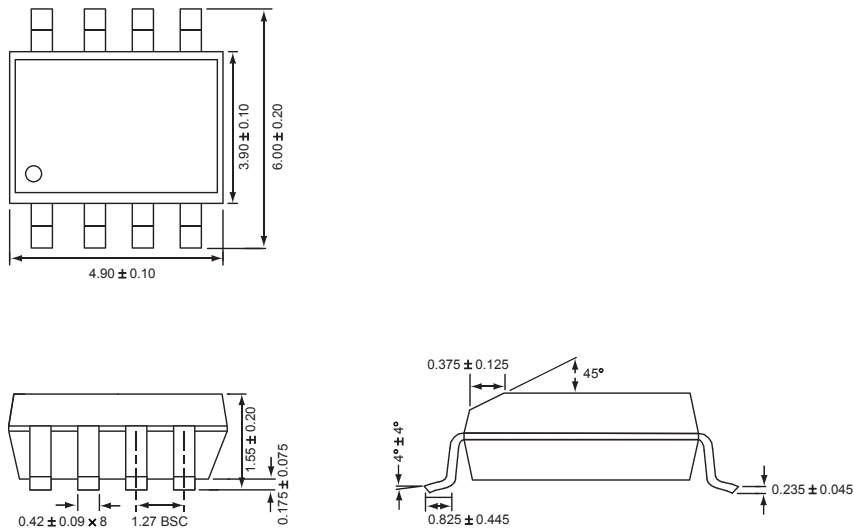
### Ordering Information

Package	Marking	Part Number (Tape and Reel)
SOP-8	7126	<b>AAT7126IAS-T1</b>

Note: Sample stock is generally held on all part numbers listed in **BOLD**.

### Package Information

#### SOP-8



All dimensions in millimeters.

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